



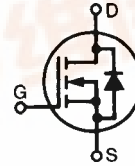
ADVANCE TECHNICAL INFORMATION

MegaMOS™ FET

IXTC 75N10

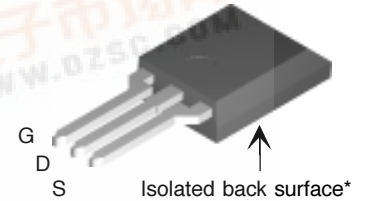
$$\begin{aligned} V_{DSS} &= 100 \text{ V} \\ I_{D25} &= 72 \text{ A} \\ R_{DS(on)} &= 20 \text{ m}\Omega \end{aligned}$$

N-Channel Enhancement Mode



Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	100	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1 \text{ M}\Omega$	100	V
V_{GS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	72	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	300	A
P_D	$T_C = 25^\circ\text{C}$	230	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
M_d	Mounting torque	1.13/10	Nm/lb.in.
Weight		2	g
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$

ISOPLUS 220™



G = Gate, D = Drain,
S = Source

* Patent pending

Features

- International standard packages
- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Low package inductance ($< 5 \text{ nH}$)
- easy to drive and to protect
- Fast switching times

Applications

- Switch-mode and resonant-mode power supplies
- Motor controls
- Uninterruptible Power Supplies (UPS)
- DC choppers

Advantages

- Easy to mount with 1 screw (TO-247) (isolated mounting screw hole)
- Space savings
- High power density

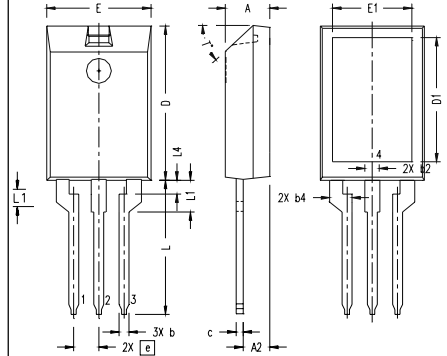
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$	100		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu\text{A}$	2		4 V
I_{GSS}	$V_{GS} = \pm 20 \text{ V}$, $V_{DS} = 0$			$\pm 100 \text{ nA}$
I_{DSS}	$V_{DS} = 0.8 V_{DSS}$, $V_{GS} = 0 \text{ V}$ $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$			200 μA 1 mA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = I_T$ Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $d \leq 2\%$			0.020 Ω



Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$V_{DS} = 10\text{ V}; I_D = I_T$, pulse test	25	30	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		4500	pF
C_{oss}			1300	pF
C_{rss}			550	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5\text{ } V_{DSS}, I_D = I_T$ $R_G = 2\text{ }\Omega$, (External)		40	60 ns
t_r			60	110 ns
$t_{d(off)}$			100	140 ns
t_f			30	60 ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5\text{ } V_{DSS}, I_D = I_T$		180	260 nC
Q_{gs}			30	70 nC
Q_{gd}			90	160 nC
R_{thJC}			0.30	0.54 K/W
R_{thCK}				K/W

Source-Drain Diode		Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
Symbol	Test Conditions	min.	typ.	max.
I_S	$V_{GS} = 0\text{ V}$			75 A
I_{SM}	Repetitive; pulse width limited by T_{JM}			300 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\text{ }\mu\text{s}$, duty cycle $d \leq 2\%$			1.75 V
t_{rr}	$I_F = I_S, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$	300		ns

Note: 1. $I_T = 37.5\text{ A}$

ISOPLUS220 OUTLINE


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.157	.197	4.00	5.00
A2	.098	.118	2.50	3.00
b	.035	.051	0.90	1.30
b2	.049	.065	1.25	1.65
b4	.093	.100	2.35	2.55
c	.028	.039	0.70	1.00
D	.591	.630	15.00	16.00
D1	.472	.512	12.00	13.00
E	.394	.433	10.00	11.00
E1	.295	.335	7.50	8.50
e	.100	BASIC	2.55	BASIC
L	.512	.571	13.00	14.50
L1	.118	.138	3.00	3.50
L4	.039	.059	1.00	1.50
T*			42.5°	47.5°

Note: All terminals are solder plated.

- 1 - Gate
- 2 - Drain
- 3 - Source